Form PTO 1449 (Modified) — U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

LIST OF REFERENCES CITED BY APPLICANT

ATTY DOCKET NO.	SERIAL NO.
240547US2	10/623,563
APPLICANT: Yukio NISHIDA, et al.	
FILING DATE: July 22, 2003	GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	2002/0100945 A1	08/01/2002	J. A. MANDELMAN, et al.			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES	TRANSLATION NO
	AO	2002-222947	08/09/2002	JAPAN (with English extract)		X
	AP	2002-305287	10/18/2002	JAPAN (with corr. US 2002/1011945 A1)		X
	AQ	9-82958	03/28/97	JAPAN (with English extract)		X
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AW	T. GHANI, et al., IEDM Technical Digest, pages 415-418, "100 NM GATE LENGTH HIGH PERFORMANCE / LOW POWER CMOS TRANSISTOR STRUCTURE", 1999
	AX	T. MATSUMOTO, et al., IEDM Technical Digest, pages 219-222, "70 NM SOI-CMOS OF 135 GHz f_{max} WITH DUAL OFFSET-IMPLANTED SOURCE-DRAIN EXTENSION STRUCTURE FOR RF/ANALOG AND LOGIC APPLICATIONS", 2001
	AY	K. OTA, et al., Extended Abstracts of the 2001 International Conference on Solid State Devices and Materials, pages 148-149, "80 NM HIGH PERFORMANCE CMOSFET WITH LOW GATE LEAKAGE CURRENT USING CONVENTIONAL THIN GATE NITRIC OXIDE", 2001
	AZ	

☐ Additional References sheet(s) attached

Examiner: [signature] Date Considered 10-29-4

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.